

LIST OF CONTRIBUTIONS TO NATIONAL AND INTERNATIONAL CONGRESSES 2018

1. I. Vila, A. Garcia, E. Curras, G. Gomez, J. Gonzalez, J. Duarte, M. Fernandez, R. Jaramillo, S. Hidalgo.
An in-depth study of Inverse-LGAD sensors.
13th "Trento" Workshop on Advanced Silicon Radiation Detectors; International
2. S. Hidalgo; M. Carulla; A. Doblas; D. Flores; A. Merlos; G. Pellegrini; D. Quirion.
CNM activities on LGADs for ATLAS/CMS Timing Layers.
32nd RD50 Workshop; International
3. X. Jordà, X. Perpiñà, M. Vellvehi, D. Sánchez, A. García-Bediaga.
Thermal Characterization of SMD Packaged 650V GaN HEMTs Assembled in PCB Board.
GaN Marathon 2.0; International
4. M. Vellvehi, X. Perpiñà, D. Sánchez, P. Fernández-Martínez, D. Flores and X. Jordà.
Failure Analysis in Power Devices using Lock-in Infrared Thermography.
Proceedings of Thermal, Mechanical and Multiphysics Simulation and Experiments in Micro-Electronics and Micro-Systems Conference (EuroSIME 2018)
5. F. Torregrossa, Y. Spiegel, L. Roux, G. Sempere, G. Borvon, T. Wuebben, W. Schustereder, M. Jelinek, F. Morancho, P. Godignon, M. Zielinski.
Advantages and Challenges of Plasma Immersion Ion Implantation for Power Devices Manufacturing on Si, SiC and GaN using PULSION® Tool.
22nd International Conference on Ion Implantation Technology (IIT), Würzburg, Germany, pp. 33-37, 2018
6. M. Campos-Aranda, I. Martín-Fernández, J.D. Alché.
LM approaches to the imaging and taxonomical identification of pollen intake by *Chrysoperla carnea* s.l. adults.
Spanish Portuguese Meeting for Advanced Optical Microscopy (SPAOM2018). International
7. I. Martín-Fernández, X. Illa, E. Masvidal-Codina, E. Prats-Alfonso, A. Guimerà-Brunet, R. Villa, P. Godignon.
Integration of CVD graphene for wafer scale fabrication of Devices.
Graphene Week 2018

8. E. Masvidal-Codina, X. Illa, M. Dasilva, A. Bonaccini, E. Prats-Alfonso, J. Martínez-Aguilar, C. Hébert, E. Del Corro Garcia, I. Martín-Fernandez, J. Bousquet, R. Villa, M. Sanchez-Vives, J. A. Garrido, A. Guimerà-Brunet.
Graphene transistors for ultra-slow frequency (< 0.1Hz) in vivo neural recording.
Graphene 2018
9. V. Soler, M. Cabello, V. Banu, J. Montserrat, J. Rebollo, P. Godignon, E. Bianda, L. Knoll, L. Kranz, A. Mihaila.
Dynamic characterization and robustness test of high voltage SiC MOSFETs.
European Conference on Silicon Carbide & Related Materials (ECSCRM)
10. M. Cabello, V. Soler, D. Haasmann, J. Montserrat, J. Rebollo, P. Godignon.
Evidence of channel mobility anisotropy on 4H-SiC MOSFETs with low interface trap density.
European Conference on Silicon Carbide & Related Materials (ECSCRM)
11. V. Soler, M. Cabello, V. Banu, J. Montserrat, J. Rebollo, P. Godignon.
Temperature behavior of complementary SiC MOSFETs for CMOS integration.
European Materials Research Society (E-MRS) Fall Meeting
12. V. Soler, M. Cabello, V. Banu, J. Montserrat, E. Bianda, L. Knoll, L. Kranz, A. Mihaila, J. Rebollo, P. Godignon.
Caracterización dinámica y tests de robustez de MOSFETs de SiC de alta tensión.
IEEE 25th Seminario Anual de Automática, Electrónica Industrial e Instrumentación (SAAEI)
13. P. Godignon, G. Rius, M. Cabello, V. Soler, J. Rebollo, J. Montserrat.
Gallium Oxide as the next semiconductor for power devices.
IEEE 25th Seminario Anual de Automática, Electrónica Industrial e Instrumentación (SAAEI)
14. Maria Cabello, Victor Soler, Lars Knoll, Josep Montserrat, Jose Rebollo, Andrei Mihaila and Philippe Godignon.
Comparative study of boron doped gate oxide impact on 4H and 6H-SiC n-MOSFETs
European Materials Research Society (E-MRS) Fall Meeting
15. C. Couso, D. Flores, S. Hidalgo, D. Quirion, M. Ullán.
Multi-Ring JFET Structure for Harsh Radiation Applications.
14th Int. Seminar on Power Semiconductors (ISPS'18)
16. C. Couso, D. Flores, S. Hidalgo, D. Quirion, M. Ullán.
Novel Radiation-Hard JFET Device Based on 3D Multi-Ring Cells.
12ª Conferencia de Dispositivos Electrónicos (CDE'18)

17. V. Banu, J. Montserrat, X. Jordà, P. Godignon.
Surface Recombination Evaluation in Bipolar Junction Transistors by Combined Electro-Optical Method.
41th International Semiconductor Conference (CAS 2018)
18. V. Banu, P. Godignon.
The Wide Band-gap Semiconductors, a New Trend of Power Semiconductor Devices Development.
Forum Romanians in micro-and nanoelectronics
19. X. Jordà, A. Avila, A. Garcia-Bediaga, X. Perpiñà, M. Vellvehi.
Analysis of Natural Convection Cooling Solutions For GaN HEMT Transistors. European Power Electronics (EPE'18-ECCE EUROPE)
20. A. Avila, A. Garcia-Bediaga, F. González, X. Jordà, X. Perpiñà, A. Rojas.
Thermal Performance Analysis of GaN-Based High-Power Converters.
European Power Electronics (EPE'18-ECCE EUROPE)